

STARPOWER

SEMICONDUCTOR

FRED

FD200HFH120C1S

Molding Type Module

1200V/200A 2 in one-package

General Description

STARPOWER Diode Power Module provides low forward voltage as well as low reverse recovery loss. They are designed for the applications such as SMPS.

Features

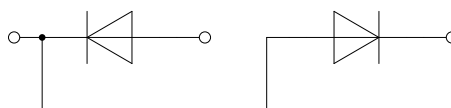
- Fast soft diode
- Low forward voltage drop
- Small temperature coefficient
- Low reverse recovery losses
- High ruggedness
- Low inductance
- Isolated copper baseplate using DBC technology



Typical Applications

- SMPS
- PFC
- Electric welders
- DC choppers

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Continuous Forward Current	200	A
I_{FRM}	Repetitive Peak Forward Current	400	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	771	W
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	2500	V

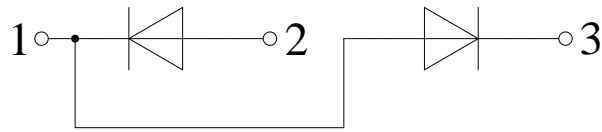
Electrical Characteristics of Diode $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=200\text{A}, T_j=25^{\circ}\text{C}$		1.82	2.27	V
		$I_F=200\text{A}, T_j=125^{\circ}\text{C}$		1.95		
Q_r	Recovered Charge	$I_F=200\text{A}, V_R=600\text{V}$ $-di/dt=3200\text{A}/\mu\text{s}$ $T_j=25^{\circ}\text{C}$		25.2		μC
I_{RM}	Peak Reverse Recovery Current			196		A
E_{rec}	Reverse Recovery Energy			8.5		mJ
Q_r	Recovered Charge	$I_F=200\text{A}, V_R=600\text{V}$ $-di/dt=3200\text{A}/\mu\text{s}$ $T_j=125^{\circ}\text{C}$		33.6		μC
			I_{RM}	Peak Reverse Recovery Current		236
E_{rec}	Reverse Recovery Energy			14.5		mJ

Thermal Characteristics

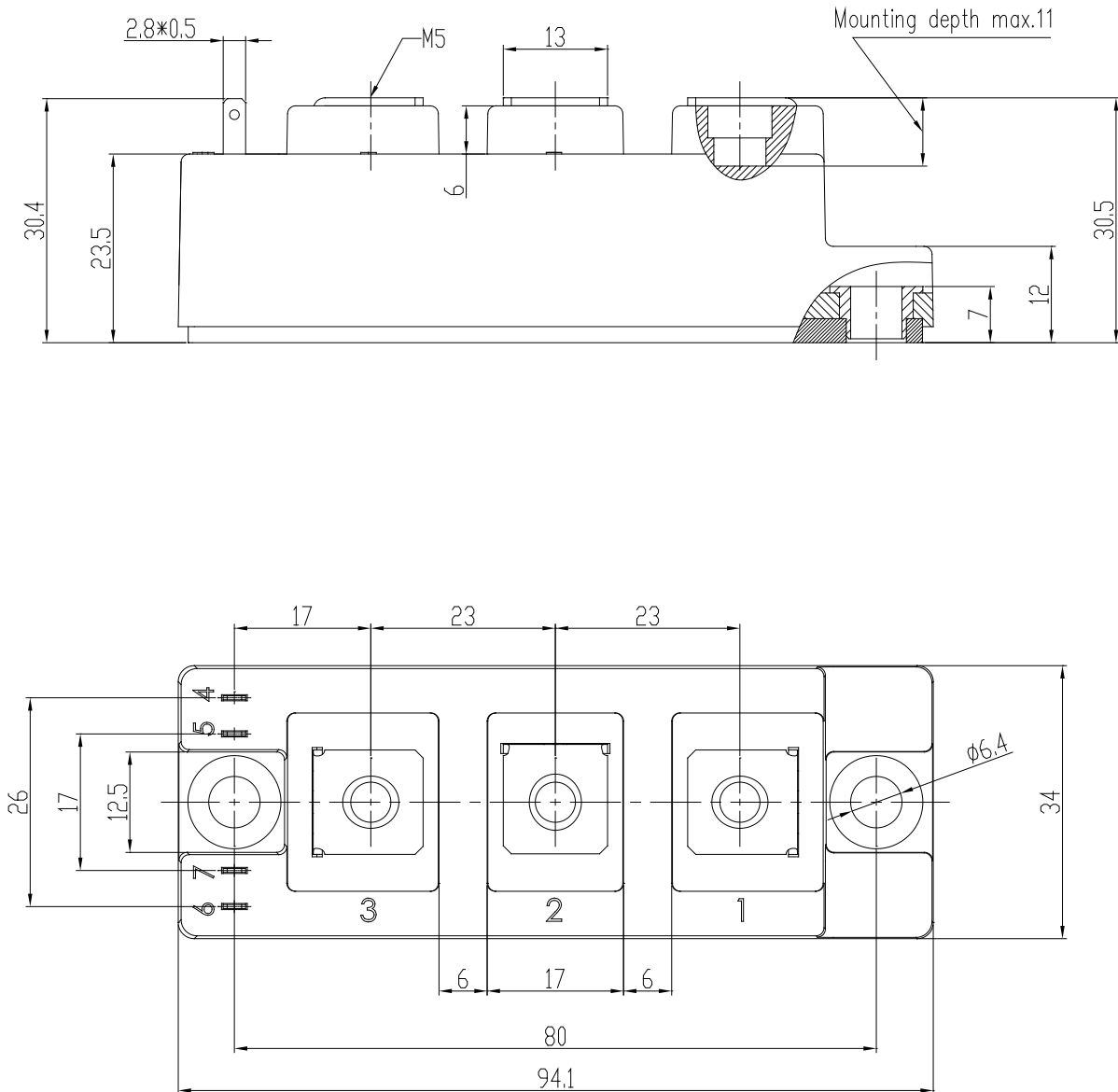
Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			30	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.75		m Ω
R_{thJC}	Junction-to-Case (per Diode)			0.162	K/W
R_{thCH}	Case-to-Heatsink (per Module)		0.050		K/W
M	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		150		g

Equivalent Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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